

#### **Public Products List**

Publict Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

PCI Title: New Lead frame supplier in CARSEM China for selected products in WFDFPN 2x3

PCI Reference: AMS/22/13685

Subject: Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

STEF512SRDBPUR	STEF512SRXCPUR	

#### **IMPORTANT NOTICE - PLEASE READ CAREFULLY**

Subject to any contractual arrangement in force with you or to any industry standard implemented by us, STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics - All rights reserved





#### Analog, MEMS & Sensors Group **Quality and Reliability**

REL 6088-1734-W-2022

# Reliability Evaluation Report STEF512SRX, STEF512SRDB

New Lead Frame Mitsui China

**General Information** 

Product Line UBFN01, UBCD01

P/N STEF512SRX, STEF512SRDB

**Product Division** 

DFN10 2x3 Package BCD8SP Silicon Process Technology

Location	
Wafer Fab	CM5F-Catania CTM8
Assembly Plant	SC-CARSEM-China
Results	
Reliability	PASS
Assessment	

#### **DOCUMENT INFORMATION**

	Version	Date	Pages	Prepared by	Approved by	Comment
ĺ	1.0	12/08/22	5	Ivan Grasso	Giuseppe Lisi	

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.

# **ST Confidential**



## Analog, MEMS & Sensors Group Quality and Reliability

REL 6088-1734-W-2022

#### **TABLE OF CONTENTS**

1	APPL	ICABLE AND REFERENCE DOCUMENTS	.3
2	GLOS	SSARY	.3
		ABILITY EVALUATION OVERVIEW	
		Objectives	
		CONCLUSION	
4	TEST	S RESULTS SUMMARY	. 4
	4.1	TEST PLAN AND RESULTS SUMMARY	. 4
	42	TESTS DESCRIPTION	5

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.



#### Analog, MEMS & Sensors Group Quality and Reliability

REL 6088-1734-W-2022

## 1 APPLICABLE AND REFERENCE DOCUMENTS

Document reference	Short description
JESD47	Stress-Test-Driven Qualification of Integrated Circuits

## **2 GLOSSARY**

Item	Short description
Tj	Temperature at junction of the device
T <sub>A</sub>	Temperature of ambient air
RH	Relative Humidity
Vcc max	Max Operative Voltage

#### **3 RELIABILITY EVALUATION OVERVIEW**

## 3.1 Objectives

This report is intended to provide reliability results for STEF512SRX diffused in BCD8sp process technology, a dual electronic fuse packaged in QFN 2x3 10L at SC-CARSEM-China with **new Lead Frame Mitsui China**. Results are referred to the reliability stress tests performed on STEF512SRX.

## 3.2 Conclusion

Qualification requirements have been fulfilled without exception. Reliability tests have shown that the devices behave correctly against environmental tests (no failure). The stability of electrical parameters during the accelerated tests demonstrates the ruggedness of the products and safe operation, which is consequently expected during their lifetime.

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.



#### Analog, MEMS & Sensors Group Quality and Reliability

**ST Confidential** 

REL 6088-1734-W-2022

## **4 TESTS RESULTS SUMMARY**

ST refers to the JEDEC standard JESD47 when conducting reliability tests for the qualification of new product.

## 4.1 Test plan and results summary

Package qualification tests

Stress (Abbv.)	Ref. Conditions			Requirements			Notes
Stress (ADDV.)	Rei. Collations	# Lot	SS	Duration	Results	Notes	
MSL Preconditioning Must be performed prior to: THB, HAST, TC, AC, & UHAST	JESD22 A113 J-STD-020	Preconditioning: (Test @ Rm) SMD only; Moisture Preconditioning for THB/HAST, AC/UHST, TC, & PTC; Peak Reflow Temp = 260C			MSL1		
High Temperature Storage Life (HTSL)	JESD22 A103	T <sub>A</sub> ≥ 150°C	3 Lots	77	1000hrs	0/231	
Temperature-Humidity- Bias (THB)	JESD22 A101	THB, 85°C, 85% RH Vcc max	3 Lots	77	1000hrs	0/231	1
Unbiased Highly Accelerated Temperature and Humidity Stress (UHAST)	JESD22 A118	uHAST, 130°C, 85%RH	3 Lots	77	96hrs	0/231	1
Temperature Cycling (TC)	JESD22 A104	C -65°C to +150°C	3 Lots	77	500cycles	0/231	1

#### Notes:

1. Preconditioning with soak per J-STD-020 at rated moisture sensitivity level prior to acceleration stress testing.

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.





## Analog, MEMS & Sensors Group Quality and Reliability

REL 6088-1734-W-2022

# 4.2 **Tests Description**

Test name	Description	Purpose				
Package Oriented						
MSL Preconditioning must be performed prior to: THB, HAST, TC, AC, & UHAST	The device is submitted to a typical temperature profile used for surface mounting devices, after a controlled moisture absorption.	As stand-alone test: to investigate the moisture sensitivity level. As preconditioning before other reliability tests: to verify that the surface mounting stress does not impact on the subsequent reliability performance. The typical failure modes are "popcorn" effect and delamination.				
High Temperature Storage Life (HTSL)	The device is stored in unbiased condition at the max. temperature allowed by the package materials, sometimes higher than the max. operative temperature.	To investigate the failure mechanisms activated by high temperature, typically wire-bonds solder joint ageing, data retention faults, metal stress-voiding.				
Temperature-Humidity- Bias (THB)	The device is biased in static configuration minimizing its internal power dissipation, and stored at controlled conditions of ambient temperature and relative humidity.	To evaluate the package moisture resistance with electrical field applied, both electrolytic and galvanic corrosion are put in evidence.				
Autoclave (AC)	The device is stored in saturated steam, at fixed and controlled conditions of pressure and temperature.	To investigate corrosion phenomena affecting die or package materials, related to chemical contamination and package hermeticity.				
Temperature Cycling (TC)	The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere.	To investigate failure modes related to the thermo-mechanical stress induced by the different thermal expansion of the materials interacting in the die-package system. Typical failure modes are linked to metal displacement, dielectric cracking, molding compound delamination, wire-bonds failure, die-attach layer degradation.				

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.



# Comparison Material/Design of DCI LF vs MITC for part 444876 - C201005

# Change comparison-Material

Item 444876	DCI	МІТС	Remark
L/F	Malaysia	Shanghai	Different
lead frame treatment	Non Roughness	Non Roughness	same
Raw material	C194	C194	same
Second_lvl_intct	e3 Sn	e3 Sn	same
Shelf life	2 year	2 year	same



# Change comparison- Design

444876		DCI	MITC	Decription
Supplier		Malaysia	Shanghai	Different
Tie bar on lead#1,5,6,10 No tie bar		Have tie bar	Different	
LF unit design	Drawing			MIT propose add tie bar in long lead#1,5,6,10 to avoid lead deformation and get the good lead coplanarity performance for this FC product .
	Side view have metal tie bar shape exposed	Side view cannot see the tie bar	Side view can see the tie bar after PKG saw	
PKG Outline	e Drawing		5 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	POD side view is different
Others(plating)		Bare copper	Bare copper	Plating is same



# Our technology starts with You



© STMicroelectronics - All rights reserved.

ST logo is a trademark or a registered trademark of STMicroelectronics International NV or its affiliates in the EU and/or other countries. For additional information about ST trademarks, please refer to <a href="https://www.st.com/trademarks">www.st.com/trademarks</a>.

All other product or service names are the property of their respective owners.



For further support in creating a PowerPoint presentation, including graphic assets, formatting tools and additional information on the ST brand

you can visit the ST Brand Portal <a href="https://brandportal.st.com">https://brandportal.st.com</a>



